

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) An electro-optical device comprising:
  - a thin film transistor formed above a substrate;
  - a pixel electrode electrically connected to a drain region of a semiconductor layer of said thin film transistor;
  - a storage capacitor having a first capacitor electrode which comprises said drain region and a second capacitor electrode;
  - an intermediate conductive layer for electrically connecting said drain region of said semiconductor layer of said thin film transistor and said pixel electrode, said intermediate conductive layer disposed between a layer of said second capacitor and a layer of said pixel electrode;
  - an upper conductive layer disposed between a layer of said intermediate conductive layer and said layer of said pixel electrode; and
  - a first contact hole formed in an area under said upper conductive layer, said first contact hole serving to electrically connect to said drain region of said semiconductor layer of said thin film transistor to said intermediate conductive layer.
2. (Previously Presented) An electro-optical device, comprising:
  - a thin film transistor formed above a substrate;
  - a pixel electrode electrically connected to a drain region of a semiconductor layer of said thin film transistor;
  - a plurality of upper conductive layers disposed between a layer of said semiconductor layer of said thin film transistor and a layer of said pixel electrode;

an intermediate conductive layer that electrically connects said drain region of said semiconductor layer of said thin film transistor and said pixel electrode; and

a first contact hole formed in an area under at least one of said plurality of upper conductive layers, said first contact hole electrically connecting said drain region of said semiconductor layer of said thin film transistor to said intermediate conductive layer,

said first contact hole having a diameter that is smaller than a diameter of a second contact hole that electrically connects said intermediate conductive layer to said pixel electrode.

3. (Currently Amended) An electro-optical device, comprising:

a thin film transistor formed above a substrate;

a pixel electrode electrically connected to a drain region of a semiconductor layer of said thin film transistor;

a plurality of upper conductive layers disposed between a layer of said semiconductor layer of said thin film transistor and a layer of said pixel electrode;

an intermediate conductive layer that electrically connects said drain region of said semiconductor layer of said thin film transistor and said pixel electrode; and

a first contact hole formed in an area under at least one of said plurality of ~~lines~~ upper conductive layers, said first contact hole electrically connecting said drain region of said semiconductor layer of said thin film transistor to said intermediate conductive layer,

at least one of said plurality of upper conductive layers serving as a data line electrically connected to a source region of said semiconductor layer of said thin film transistor, and said first contact hole being located in an area under said data line.

4. (Original) The electro-optical device according to claim 3, said first contact hole being disposed near a location where said line and said scanning line cross each other.

5. (Previously Presented) The electro-optical device according to Claim 3, at least one of said plurality of upper conductive layers serving as a scanning line extending in a direction crossing said data line, and said intermediate conductive layer extending along said scanning line from an area of said data line.

6. (Original) The electro-optical device according to Claim 4, further comprising a second contact hole, via which said intermediate conductive layer and said pixel electrode are electrically connected to each other, is formed in an area where said intermediate conductive layer extends along said scanning line.

7. (Original) The electro-optical device according to Claim 6, said second contact hole being formed at a substantially middle location between adjacent data lines.

8. (Original) The electro-optical device according to Claim 3, said intermediate conductive layer extending along said data line.

9. (Previously Presented) The electro-optical device according to Claim 1, at least one of said plurality of upper conductive layers serving as a capacitance line which extends under said intermediate conductive layer while avoiding an area where said first contact hole is formed.

10. (Original) The electro-optical device according to Claim 1, said first contact hole having a depth that is smaller than a depth of a second contact hole formed between said intermediate conductive layer and said pixel electrode.

11. (Original) The electro-optical device according to claim 4, said intermediate conductive layer being disposed at least partially opposite to a capacitor electrode formed of a film forming said scanning line via an interlayer insulating film.

12. (Original) The electro-optical device according to claim 11, further comprising a second contact hole formed at a location which overlaps, in plan view, with said capacitor electrode.

13. (Original) The electro-optical device according to claim 11,  
said capacitor electrode comprising a part extending along said scanning line  
and a part extending along said data line from a location where said capacitor electrode and  
said data line cross each other, in plan view, and  
said intermediate conductive layer overlapping, at least partially, with said  
capacitance electrode via an interlayer insulating film.

14. (Original) The electro-optical device according to Claim 1, said intermediate  
conductive layer includes a light-shielding conductive film.

15. (Original) The electro-optical device according to claim 14, said intermediate  
conductive layer comprising a part of a light-shielding area.

16. (Original) The electro-optical device according to claim 15, said intermediate  
conductive layer comprising a part extending along said data line in plan view, and said part  
defining a part of said light-shielding area along said data line.

17. (Original) The electro-optical device according to claim 16, further  
comprising capacitor electrode which includes a part extending along said data line in plan  
view, and

in an area along said data line, a width  $W_d$  of said data line, a width  $W_c$  of  
said capacitor electrode, and a width  $W_m$  of the part, extending along said data line, of said  
intermediate conductive layer are selected so as to satisfy a condition  $W_d < W_c < W_m$ .

18. (Original) The electro-optical device according to claim 17, an edge portion,  
extending along said data line, of said pixel electrode overlapping with an edge portion of aid  
intermediate conductive layer.

19. (Original) The electro-optical device according to Claim 3, said  
semiconductor layer being formed in an area under said data line.

20. (Original) The electro-optical device according to Claim 19, said first contact hole being formed at a location symmetrical to the location of a third contact hole via which the source region of said semiconductor layer and said data line are connected to each other, with respect to a channel region of said semiconductor layer.

21. (Original) The electro-optical device according to Claim 19, further comprising:

a lower light shielding film which is disposed under said semiconductor layer which projects, in plan view, from said scanning line, and

a second contact hole via which said intermediate conductive layer and said pixel electrode are electrically connected to each other, the second contact hole being located in an area into which said lower light shielding film projects, in plan view, from said scanning line.

22. (Original) An electro-optical device comprising:

a thin film transistor formed on a substrate;

a data line electrically connected to a drain region of a semiconductor layer of said thin film transistor;

a pixel electrode electrically connected to a drain region of said semiconductor layer of said thin film transistor;

a light-shielding intermediate conductive layer that electrically connects the drain region of said semiconductor layer of said thin film transistor and said pixel electrode;

a capacitance line which is disposed in the drain region of said semiconductor layer of said thin film transistor and which extends along said data line;

a light-shielding film formed of a film forming said intermediate conductive layer; and

a contact hole via which said capacitance line and said light shielding film are electrically connected with each other in an area under said data line.